

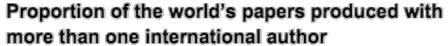
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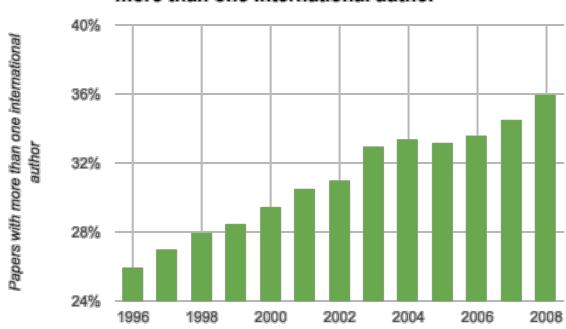
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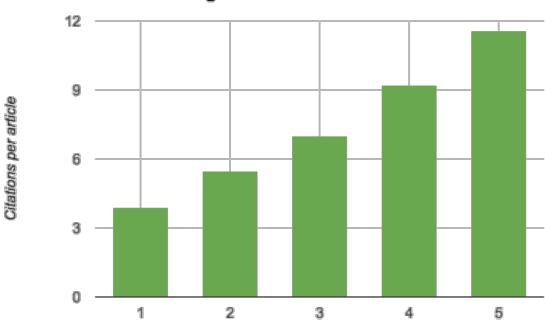


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Collaboration is highly beneficial

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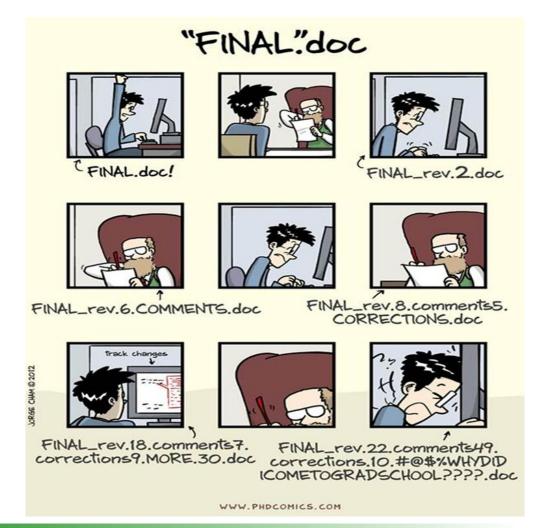


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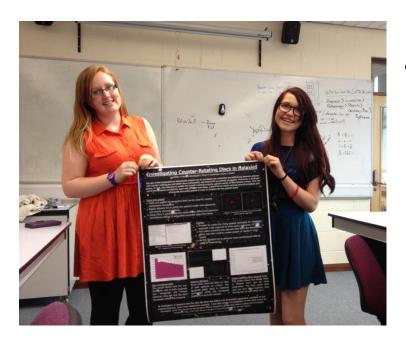
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Manual

Modeling of Trap Induced Dispersion of Large Signal Dynamic Characteristics of GaN HEMTs

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Abstract

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48 We propose here a non-linear GaN HEMT model for CAD including a trapping effects description consistent with both small-signal and large-signal operating modes. It takes into account the dynamics of the traps and then allows to accurately model the modulated large signal characteristics that are encountered in telecommunication and radar signals. This model is elaborated through low-frequency S-parameter measurements complementary to more classical pulsed-IV characterizations. A 8x75μm AllnN/GaN HEMT model was designed and particularly validated in large-signal pulsed RF operation. It is also shown that thermal and trapping effects have opposite effects on the output conductance, thus opening the way for separate characterizations of the two effects.

Modeling of Trap Induced Dispersion of Large Signal Dynamic Characteristics of GaN HEMTs

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Index Terms—Trappings effects, thermal effects, low frequency S-parameters, CAD non-linear model, RF pulsed operation.

I. INTRODUCTION

Gallium Nitride (GaN) High Electron Mobility Transistors (HEMT) on SiC are now recognized as good candidates for the development of a number of RF applications and notably Power Amplifiers (PA) for telecommunications and radars, due to their high breakdown voltage, their high cut-off frequency as well as their high temperature capabilities. However they are still subject to parasitics effects such as thermal effects and especially trapping effects. Those trapping effects have been extensively studied using a number of techniques such as pulsed measurements, load-pull measurements as well as frequency dispersion measurements. At the same time, models have been proposed that take those effects into account [1], [2], [3], and while the effects of traps are well taken into account in CW conditions, their impacts on dynamic large signal characteristics remain difficult to understand. They manifest themselves under modulated signals such as RF pulses or telecommunications signals. Memory effects are the main consequence of those trapping effects. In this paper we propose to partients the dynamics of those transing effects using large

account the dynamics of the traps. Finally we conclude and draw some perspectives.

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II. IMPACT OF TRAPS ON LARGE SIGNAL CHARACTERISTICS

One convenient way to identify the impact of trapping effects is to monitor the average drain current of the transistor versus an increasing RF input power. It has already been reported in [1] and [3] that this drain current under class-AB conditions decreases as the input power increases, contradicting the expected characteristics. Clearly this behavior cannot be explained by thermal behavior as far as the channel temperature sinks when the power increases and would leads, at least for moderate powers, to an average drain current enlargement.

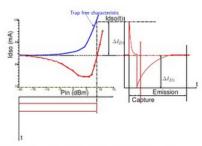
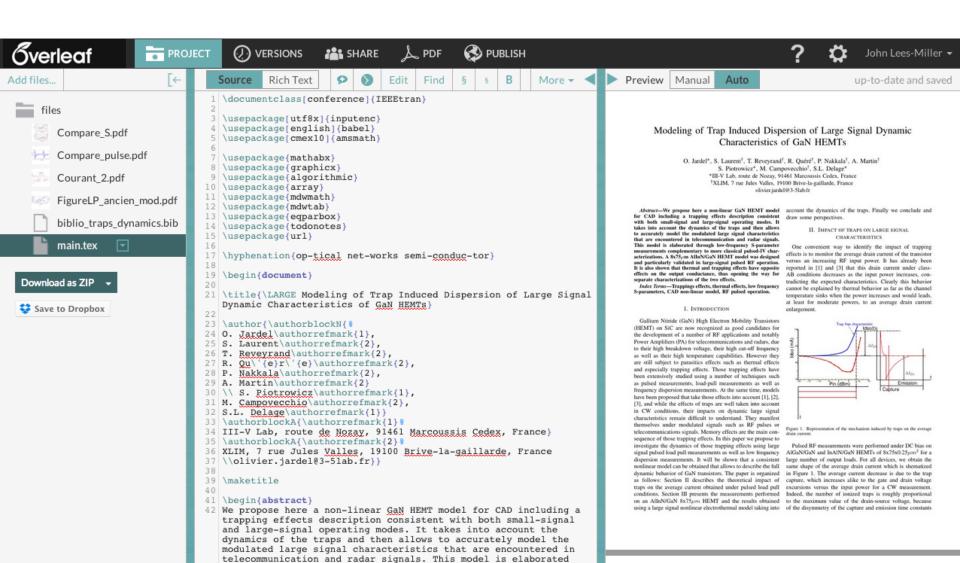


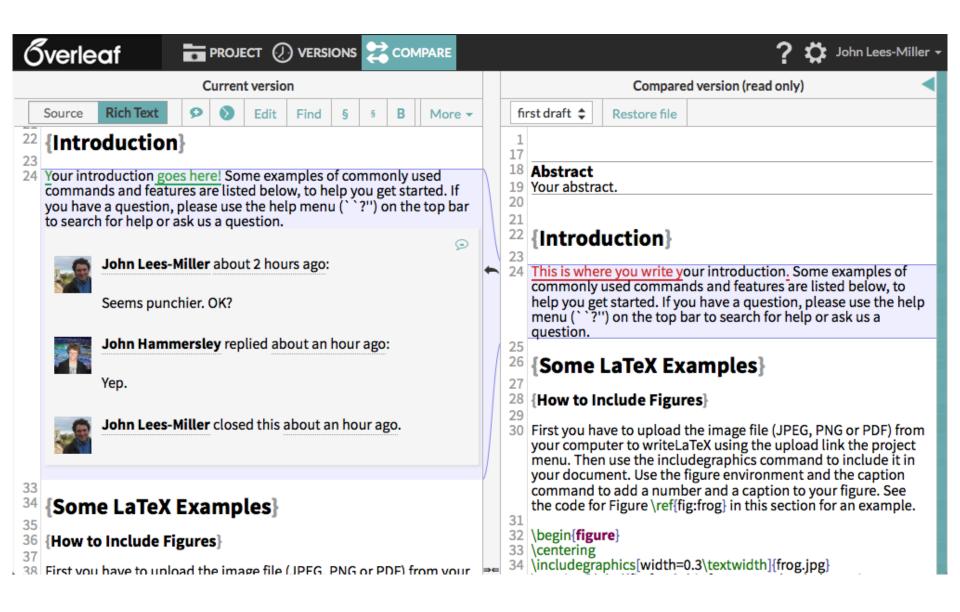
Fig. 1. Representation of the mechanism induced by traps on the average drain current.

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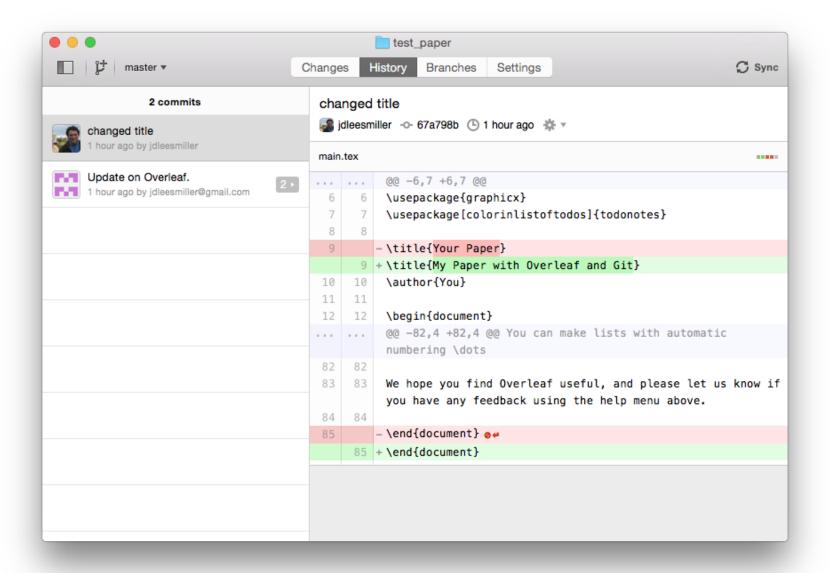




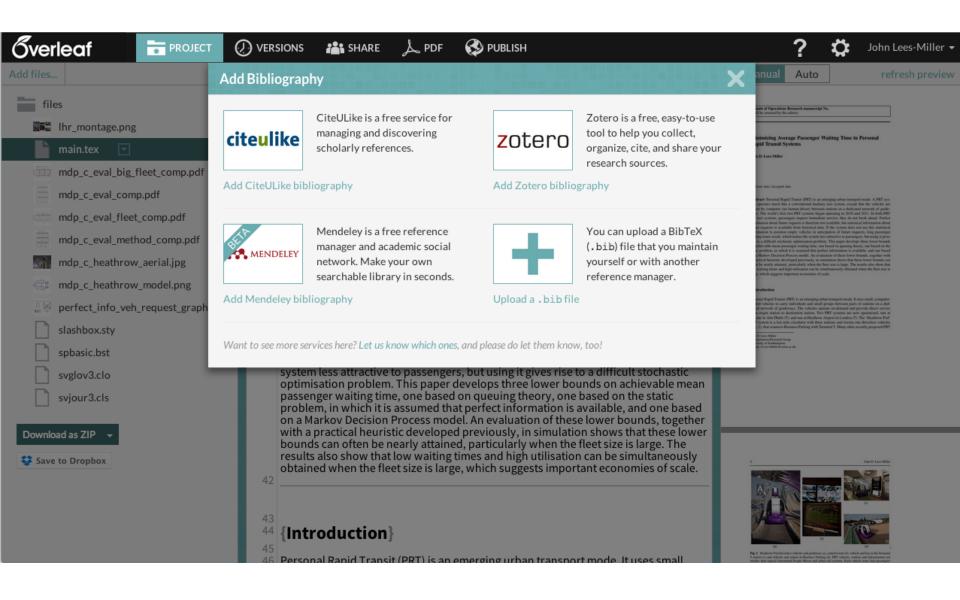




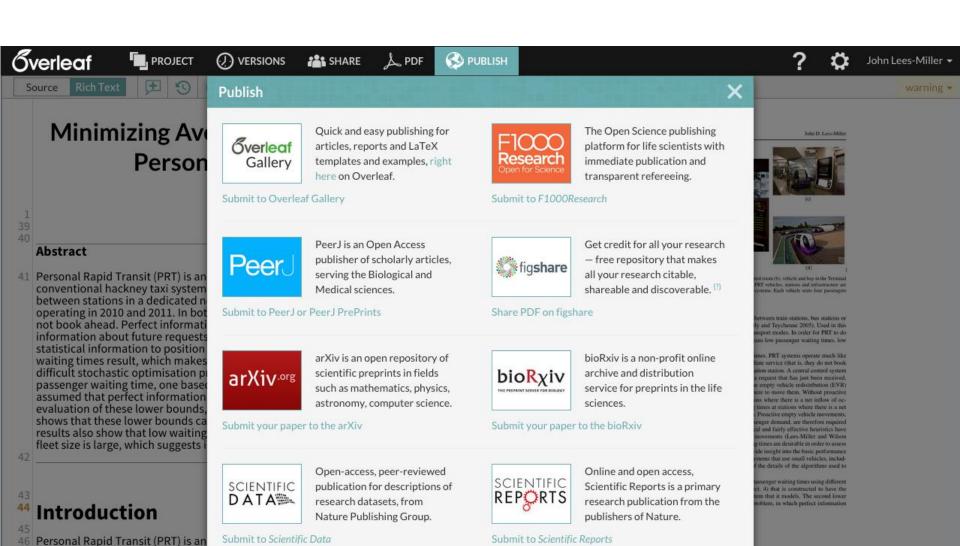












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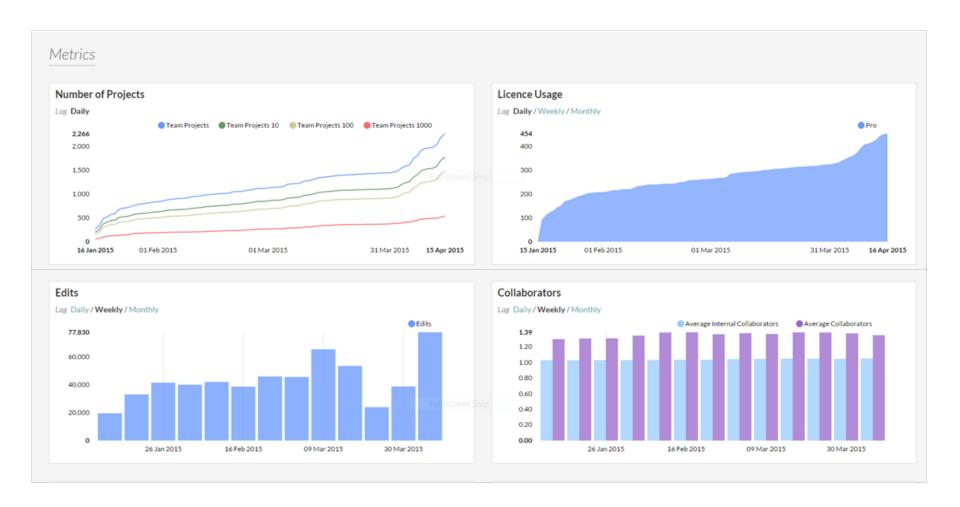
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